

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12996	(insulat\$3 or dielectric or hafnium or hf or zirconium or zr) and (substrate or wafer) and (irradiat\$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 11:45
L2	3088	1 and (irradiat\$3) with (insulat\$3 or dielectric or hafnium or hf or zirconium or zr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 11:32
L3	16	2 and (irradiat\$3) with (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 11:46
L4	61165	(insulat\$3 or dielectric or hafnium or hf or zirconium or zr) and (substrate or wafer) and (irradiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:05
L5	50	4 and (irradiat\$3) with (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 11:46
L6	39	4 and (irradiat\$3) near15 (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:06
L7	18128	((high near3 dielectric) or (hafnium or hf) or (zirconium or zr)) and (substrate or wafer) and (irradiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:06
L8	39	7 and (irradiat\$3) near15 (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:06
L9	81	7 and (irradiat\$3) near15 (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:07

L10	81	7 and ((irradiat\$3) near15 (high near3 dielectric)) with (insulat\$3 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:07
L11	13	7 and ((irradiat\$3) near15 (high near3 dielectric)) with (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:10
L12	13	7 and ((irradiat\$3) near15 (high near3 dielectric)) same (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:10
L13	37	7 and ((irradiat\$3) near15 (high near3 dielectric)) and (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:20
L14	129	7 and ((irradiat\$3) near15 (hafnium or hf)) and (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:20
L15	22	7 and ((irradiat\$3) near15 (hafnium or hf)) with (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:22
L16	33	7 and ((irradiat\$3) near15 (hafnium or hf)) same (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:23
L17	6	7 and ((irradiat\$3) near15 (zirconium or zr)) same (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:28
L18	47	7 and ((irradiat\$3) near15 (zirconium or zr)) and (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:35
L19	39272	(high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:35

L20	1302502	(irradiat\$3 or radiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:36
L21	8031	19 and 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:36
L22	583	21 and (irradia\$3 or radiat\$3) with (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:37
L23	422	21 and (irradia\$3 or radiat\$3) near10 (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:37
L24	61	23 and (method with semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:47
L25	507	(light) near10 (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:47
L26	140	25 and (radiat\$3 or radiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:47
L27	64	26 and (irradiat\$3 or radiat\$3) near5 (light)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:48
L28	11	26 and (irradiat\$3 or radiat\$3) near5 (light) with (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:50
L29	14	26 and (irradiat\$3 or radiat\$3) near5 (light) same (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:50

L30	64	26 and (irradiat\$3 or radiat\$3) near5 (light)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:56
L31	270128	(irradiat\$3 or radiat\$3) near3 (light)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:56
L32	19	((irradiat\$3 or radiat\$3) near3 (light)) near15 (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:57
L33	1476	((irradiat\$3 or radiat\$3) near3 (light)) and (high near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 12:58
L34	199	33 and (radiat\$3 or irradiat\$3) with (crystal\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:08
L35	2050	(laser or beam or light) near15 (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:09
L36	393	35 and (irradiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:10
L37	306	36 and (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:22
L38	234	36 and (substrate or wafer) with (insulat\$3 or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:22
L39	234	38 and (laser or beam or light) with (high near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:23

L40	24	38 and (laser or beam or light) with (high near3 dielectric) with (insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/18 13:24
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